

# NGB8202N, NGB8202AN

## Ignition IGBT

### 20 A, 400 V, N-Channel D<sup>2</sup>PAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Overvoltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

#### Features

- Ideal for Coil-on-Plug and Driver-on-Coil Applications
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- These are Pb-Free Devices

#### Applications

- Ignition Systems

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	440	V
Collector-Gate Voltage	V <sub>CER</sub>	440	V
Gate-Emitter Voltage	V <sub>GE</sub>	± 15	V
Collector Current-Continuous @ T <sub>C</sub> = 25°C - Pulsed	I <sub>C</sub>	20 50	A <sub>DC</sub> A <sub>AC</sub>
Continuous Gate Current	I <sub>G</sub>	1.0	mA
Transient Gate Current (t <sub>s</sub> ≤ 2 ms, f ≤ 100 Hz)	I <sub>G</sub>	20	mA
ESD (Charged-Device Model)	ESD	2.0	kV
ESD (Human Body Model) R = 1500 Ω, C = 100 pF	ESD	8.0	kV
ESD (Machine Model) R = 0 Ω, C = 200 pF	ESD	500	V
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	150 1.0	W W/°C
Operating & Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



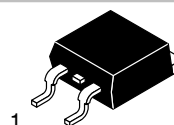
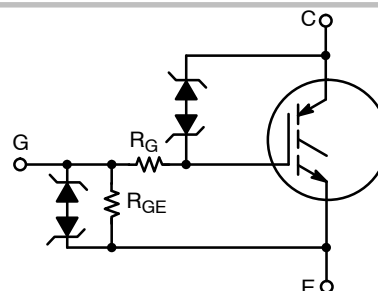
**ON Semiconductor**®

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**20 AMPS, 400 VOLTS**

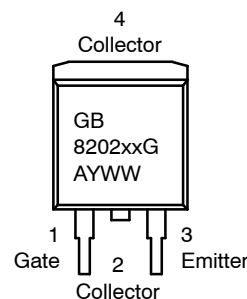
**V<sub>CE(on)</sub> = 1.3 V @**

**I<sub>C</sub> = 10 A, V<sub>GE</sub> ≥ 4.5 V**



**D<sup>2</sup>PAK  
CASE 418B  
STYLE 4**

#### MARKING DIAGRAM



GB8202xx = Device Code  
xx = N or AN  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NGB8202NT4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel
NGB8202ANT4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NGB8202N, NGB8202AN

## UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS ( $-55^{\circ} \leq T_J \leq 175^{\circ}C$ )

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , $Pk\ I_L = 16.7\text{ A}$ , $R_G = 1000\ \Omega$ , $L = 1.8\text{ mH}$ , Starting $T_J = 25^{\circ}C$ $V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , $Pk\ I_L = 14.9\text{ A}$ , $R_G = 1000\ \Omega$ , $L = 1.8\text{ mH}$ , Starting $T_J = 150^{\circ}C$ $V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , $Pk\ I_L = 14.1\text{ A}$ , $R_G = 1000\ \Omega$ , $L = 1.8\text{ mH}$ , Starting $T_J = 175^{\circ}C$	$E_{AS}$	250 200 180	mJ
Reverse Avalanche Energy $V_{CC} = 100\text{ V}$ , $V_{GE} = 20\text{ V}$ , $Pk\ I_L = 25.8\text{ A}$ , $L = 6.0\text{ mH}$ , Starting $T_J = 25^{\circ}C$	$E_{AS(R)}$	2000	mJ

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds (Note 2)	$T_L$	275	$^{\circ}C$

- When surface mounted to an FR4 board using the minimum recommended pad size.
- For further details, see Soldering and Mounting Techniques Reference Manual: SOLDERRM/D.

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	$BV_{CES}$	$I_C = 2.0\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	370	395	420	V	
		$I_C = 10\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	390	415	440		
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = 15\text{ V}$	$T_J = 25^{\circ}C$		0.1	1.0	$\mu A$	
			$T_J = 25^{\circ}C$	$V_{CE} = 200\text{ V}$ , $V_{GE} = 0\text{ V}$	0.5	1.5	10	$\mu A$
				$T_J = 175^{\circ}C$	1.0	25	100*	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75\text{ mA}$	$T_J = 25^{\circ}C$	30	35	39	V	
			$T_J = 175^{\circ}C$	35	39	45*		
			$T_J = -40^{\circ}C$	30	33	37		
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24\text{ V}$ – NGB8202N	$T_J = 25^{\circ}C$	0.05	0.1	0.5	mA	
			$T_J = 175^{\circ}C$	1.0	5.0	10		
			$T_J = -40^{\circ}C$	0.005	0.01	0.1		
			$T_J = 25^{\circ}C$	0.05	0.2	1.0		
			$T_J = 175^{\circ}C$	1.0	8.5	25		
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24\text{ V}$ – NGB8202AN	$T_J = 25^{\circ}C$	0.05	0.2	1.0	mA	
			$T_J = 175^{\circ}C$	1.0	8.5	25		
			$T_J = -40^{\circ}C$	0.005	0.025	0.2		
			$T_J = 25^{\circ}C$	0.05	0.2	1.0		
			$T_J = 175^{\circ}C$	1.0	8.5	25		
Gate-Emitter Clamp Voltage	$BV_{GES}$	$I_G = \pm 5.0\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	12	12.5	14	V	
Gate-Emitter Leakage Current	$I_{GES}$	$V_{GE} = \pm 5.0\text{ V}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	200	300	350*	$\mu A$	
Gate Resistor	$R_G$		$T_J = -40^{\circ}C$ to $175^{\circ}C$		70		$\Omega$	
Gate-Emitter Resistor	$R_{GE}$		$T_J = -40^{\circ}C$ to $175^{\circ}C$	14.25	16	25	k $\Omega$	

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0\text{ mA}$ , $V_{GE} = V_{CE}$	$T_J = 25^{\circ}C$	1.5	1.8	2.1	V
			$T_J = 175^{\circ}C$	0.7	1.0	1.3	
			$T_J = -40^{\circ}C$	1.7	2.0	2.3*	
Threshold Temperature Coefficient (Negative)				4.0	4.6	5.2	mV/ $^{\circ}C$

\*Maximum Value of Characteristic across Temperature Range.

- Pulse Test: Pulse Width  $\leq 300\ \mu S$ , Duty Cycle  $\leq 2\%$ .

# NGB8202N, NGB8202AN

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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### ON CHARACTERISTICS (Note 4)

Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.5 \text{ A}, V_{GE} = 3.7 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	0.95	1.15	1.35	V
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.15	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.4	
		$I_C = 6.5 \text{ A}, V_{GE} = 3.7 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	0.85	1.03	1.35	
			$T_J = 175^\circ\text{C}$	0.7	0.9	1.15	
			$T_J = -40^\circ\text{C}$	0.0	1.11	1.4	
		$I_C = 9.0 \text{ A}, V_{GE} = 3.9 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	0.95	1.25	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.25	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.5	
		$I_C = 9.0 \text{ A}, V_{GE} = 3.9 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	0.9	1.11	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.01	1.25	
			$T_J = -40^\circ\text{C}$	1.0	1.18	1.5	
		$I_C = 7.5 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	0.85	1.15	1.4	
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.2	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.6*	
		$I_C = 10 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.3	1.6	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.4	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.7*	
		$I_C = 15 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.15	1.45	1.7	
			$T_J = 175^\circ\text{C}$	1.0	1.3	1.55	
			$T_J = -40^\circ\text{C}$	1.25	1.55	1.8*	
		$I_C = 20 \text{ A}, V_{GE} = 4.5 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	1.3	1.6	1.9	
			$T_J = 175^\circ\text{C}$	1.2	1.5	1.8	
			$T_J = -40^\circ\text{C}$	1.4	1.75	2.0	
$I_C = 20 \text{ A}, V_{GE} = 4.5 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	1.1	1.4	1.9			
	$T_J = 175^\circ\text{C}$	1.2	1.5	1.8			
	$T_J = -40^\circ\text{C}$	1.3	1.42	2.0			
Forward Transconductance	gfs	$I_C = 6.0 \text{ A},$ $V_{CE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	10	18	25	Mhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	$C_{ISS}$	$f = 10 \text{ kHz}, V_{CE} = 25 \text{ V}$	$T_J = 25^\circ\text{C}$	1100	1300	1500	pF
Output Capacitance	$C_{OSS}$			70	80	90	
Transfer Capacitance	$C_{RSS}$			18	20	22	

# NGB8202N, NGB8202AN

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS

Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega, R_L = 33\ \Omega,$ $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	6.0	8.0	10	$\mu\text{Sec}$
			$T_J = 175^\circ\text{C}$	6.0	8.0	10	
Fall Time (Resistive)	$t_f$		$T_J = 25^\circ\text{C}$	4.0	6.0	8.0	
			$T_J = 175^\circ\text{C}$	8.0	10.5	14	
Turn-Off Delay Time (Inductive)	$t_{d(off)}$	$V_{CC} = 300\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega,$ $L = 300\ \mu\text{H}, V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	3.0	5.0	7.0	
			$T_J = 175^\circ\text{C}$	5.0	7.0	9.0	
Fall Time (Inductive)	$t_f$		$T_J = 25^\circ\text{C}$	1.5	3.0	4.5	
			$T_J = 175^\circ\text{C}$	5.0	7.0	10	
Turn-On Delay Time	$t_{d(on)}$		$V_{CC} = 14\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega, R_L = 1.5\ \Omega,$ $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.5	2.0
				$T_J = 175^\circ\text{C}$	1.0	1.5	2.0
Rise Time	$t_r$	$T_J = 25^\circ\text{C}$		4.0	6.0	8.0	
		$T_J = 175^\circ\text{C}$		3.0	5.0	7.0	

\*Maximum Value of Characteristic across Temperature Range.

4. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

# NGB8202N, NGB8202AN

## TYPICAL ELECTRICAL CHARACTERISTICS

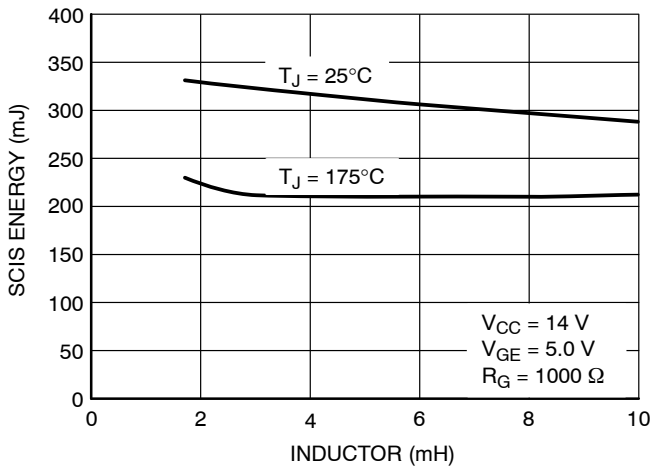


Figure 1. Self Clamped Inductive Switching

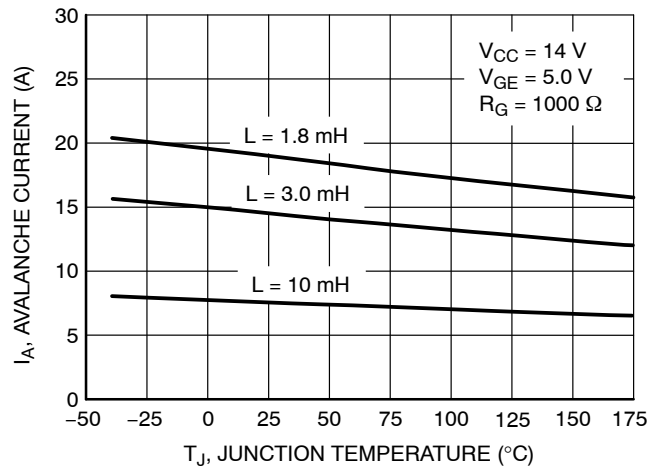


Figure 2. Open Secondary Avalanche Current vs. Temperature

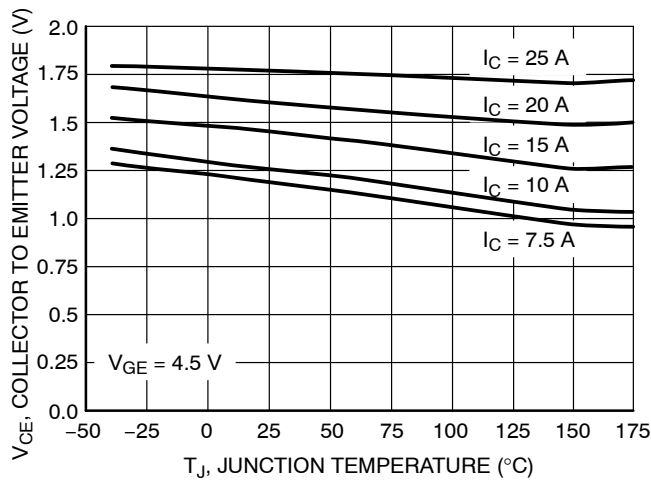


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

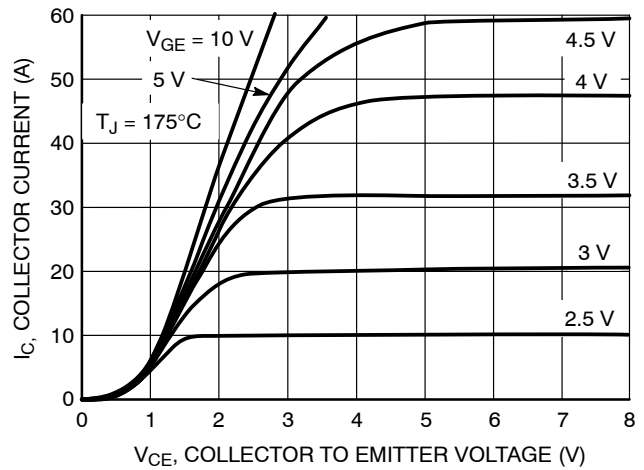


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

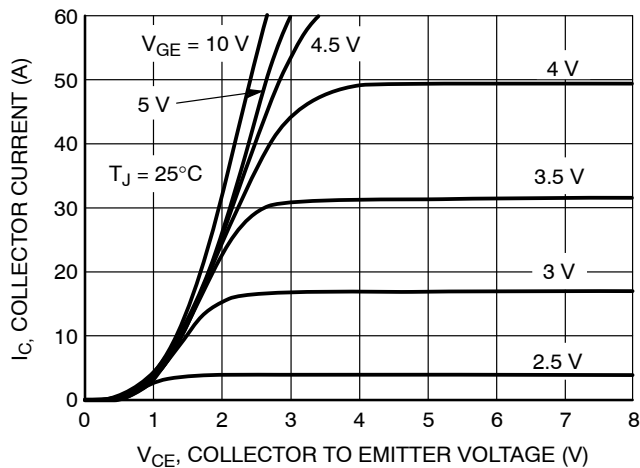


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

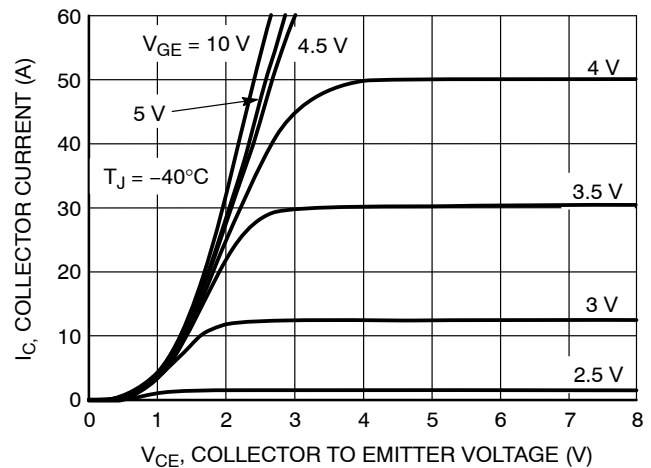


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

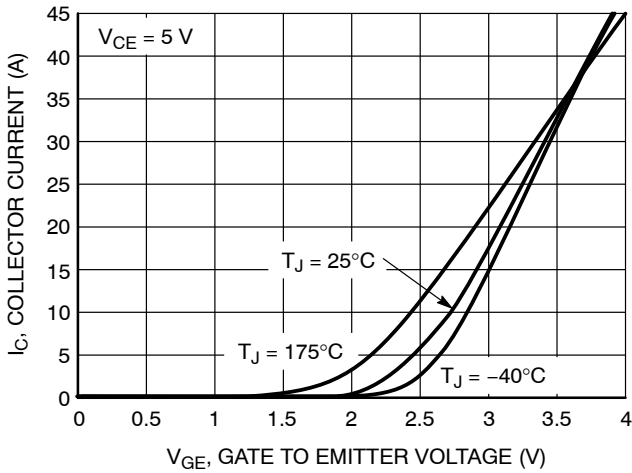


Figure 7. Transfer Characteristics

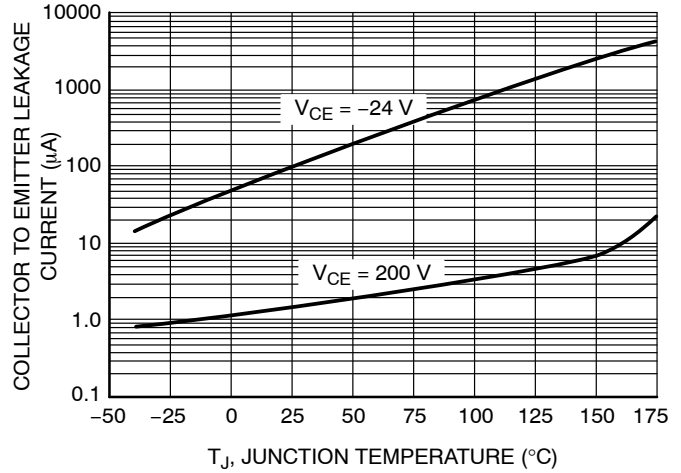


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

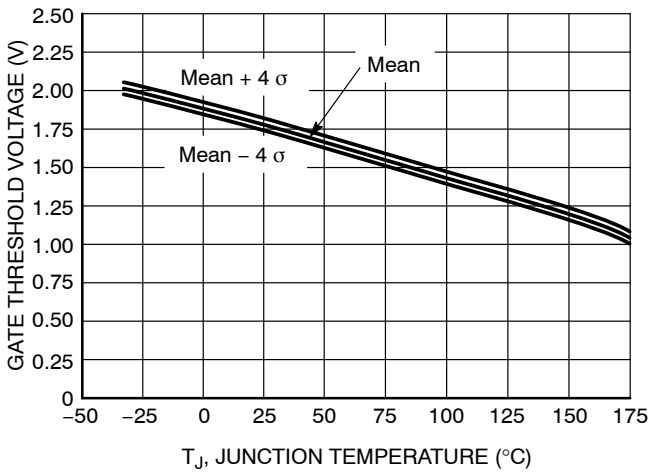


Figure 9. Gate Threshold Voltage vs. Temperature

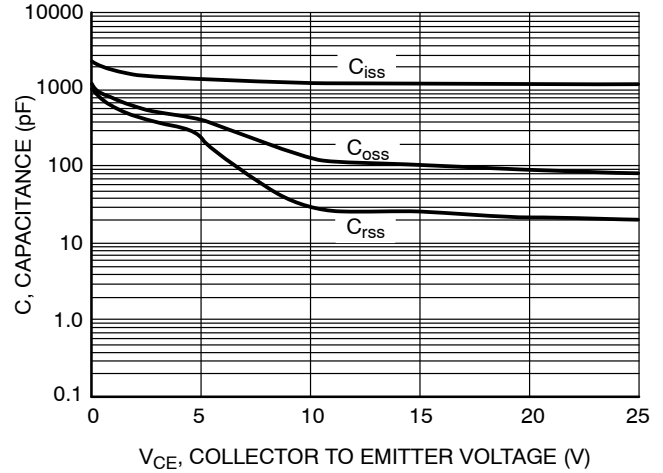


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

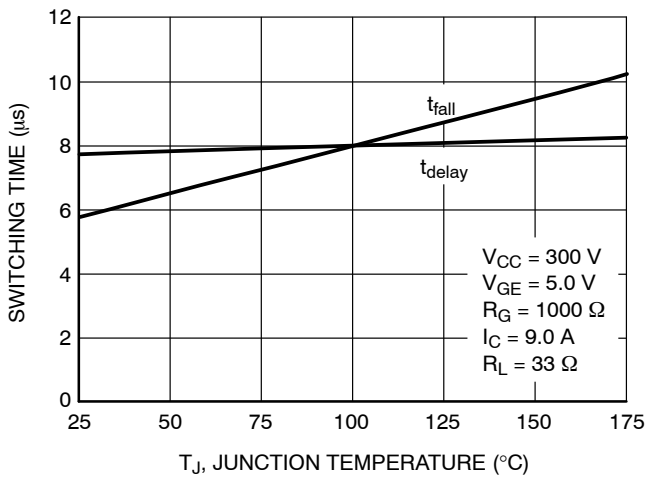


Figure 11. Resistive Switching Fall Time vs. Temperature

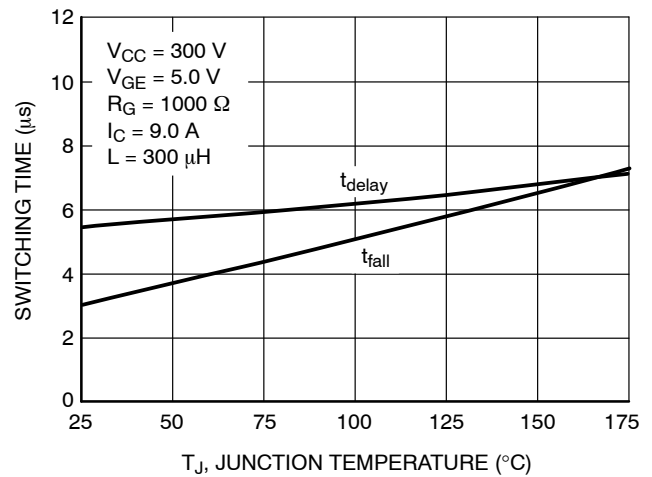
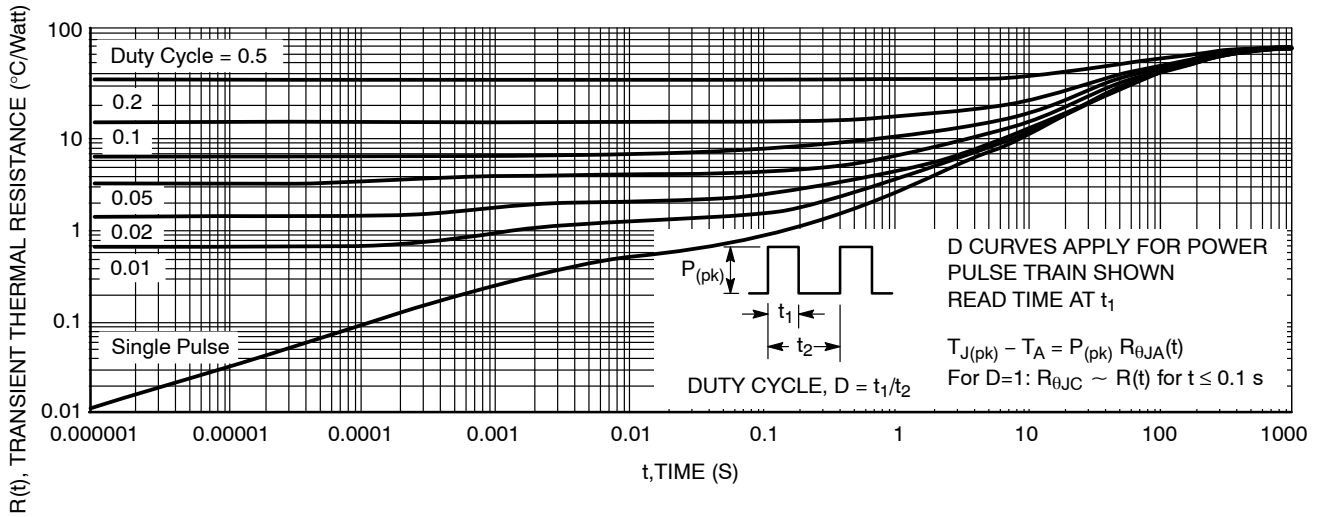
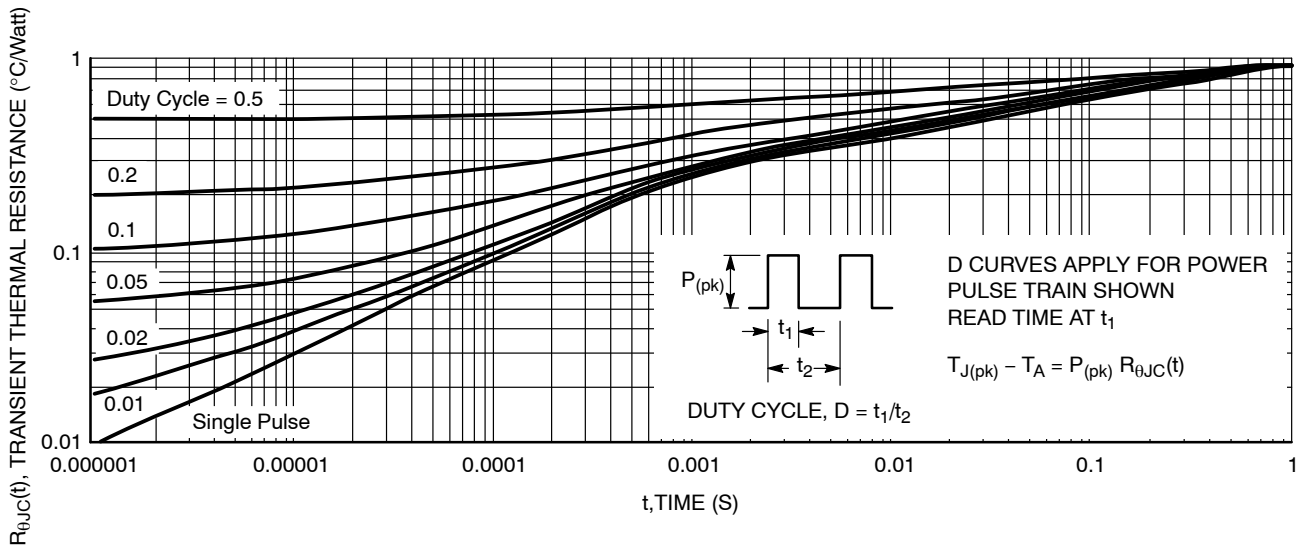


Figure 12. Inductive Switching Fall Time vs. Temperature

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**Figure 13. Minimum Pad Transient Thermal Resistance (Non-normalized Junction-to-Ambient)**

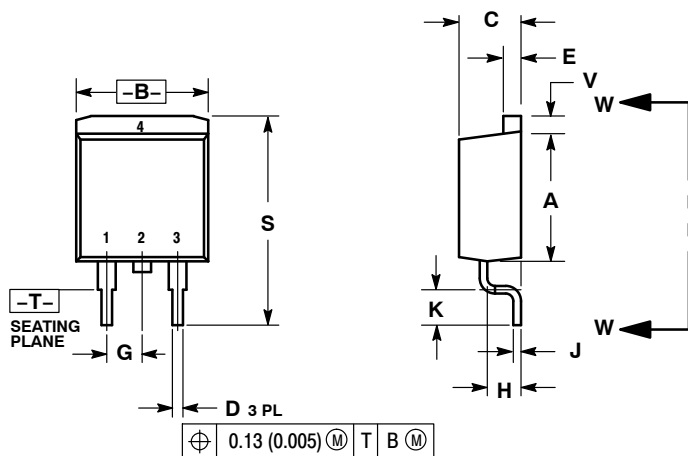


**Figure 14. Best Case Transient Thermal Resistance (Non-normalized Junction-to-Case Mounted on Cold Plate)**

# NGB8202N, NGB8202AN

## PACKAGE DIMENSIONS

### D<sup>2</sup>PAK 3 CASE 418B-04 ISSUE K



NOTES:

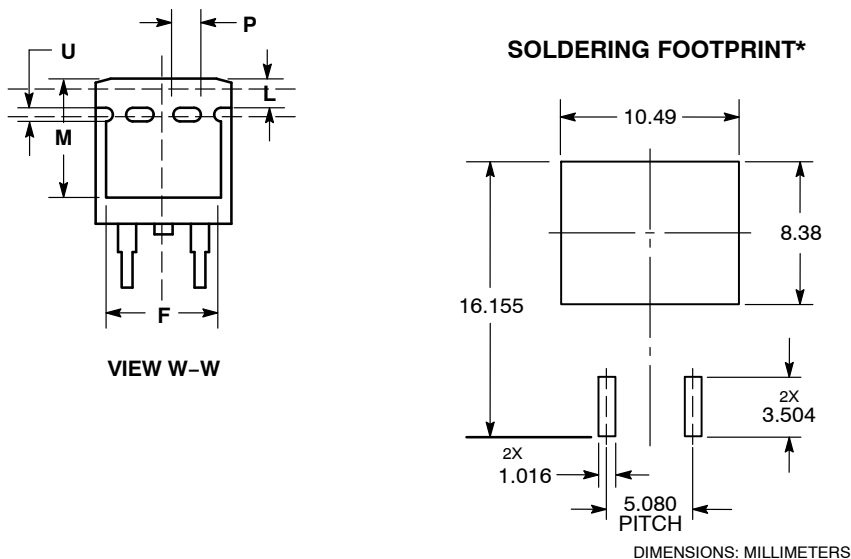
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 4:

- PIN 1. GATE
- COLLECTOR
- EMITTER
- COLLECTOR

### SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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